FIG. 1

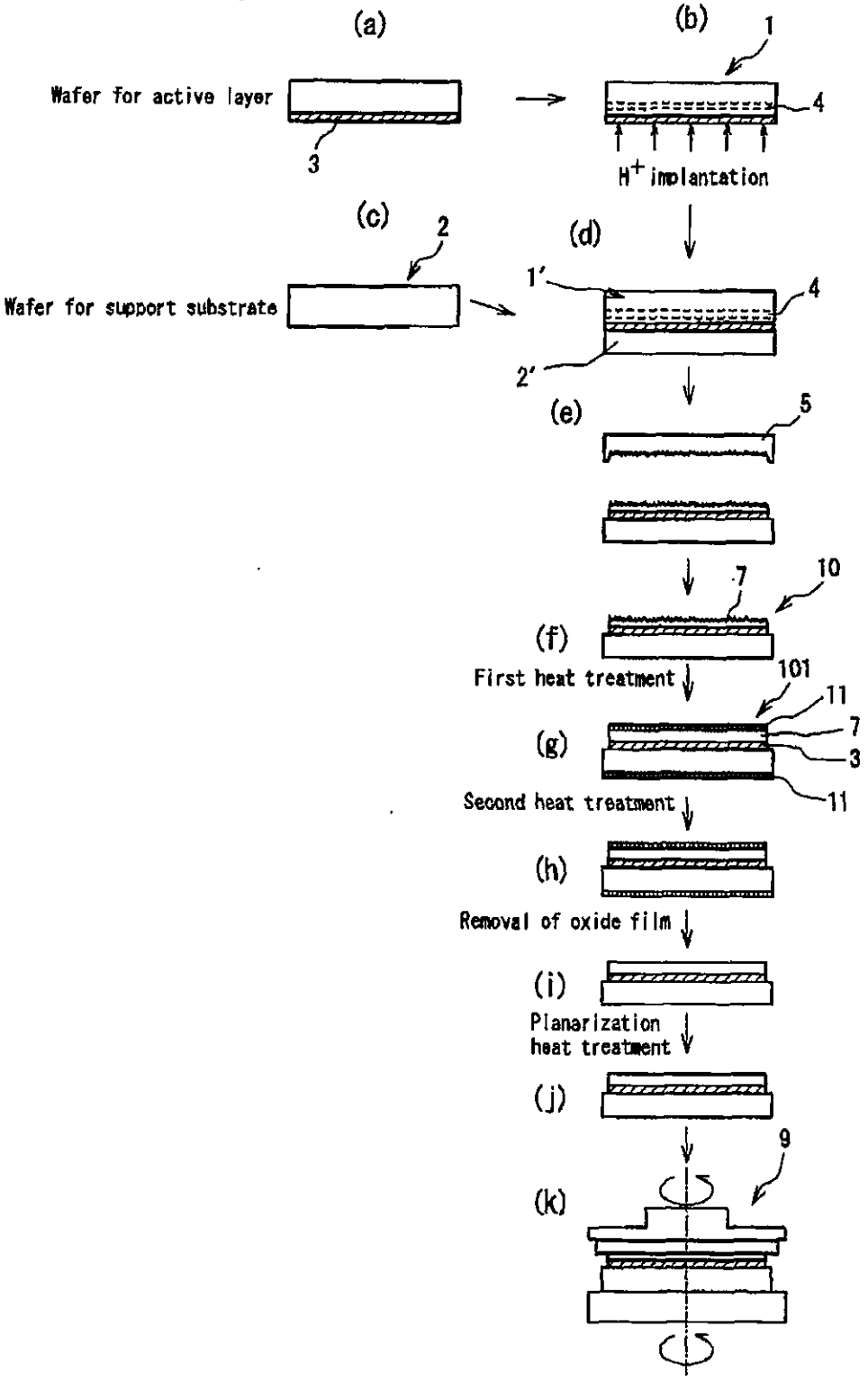
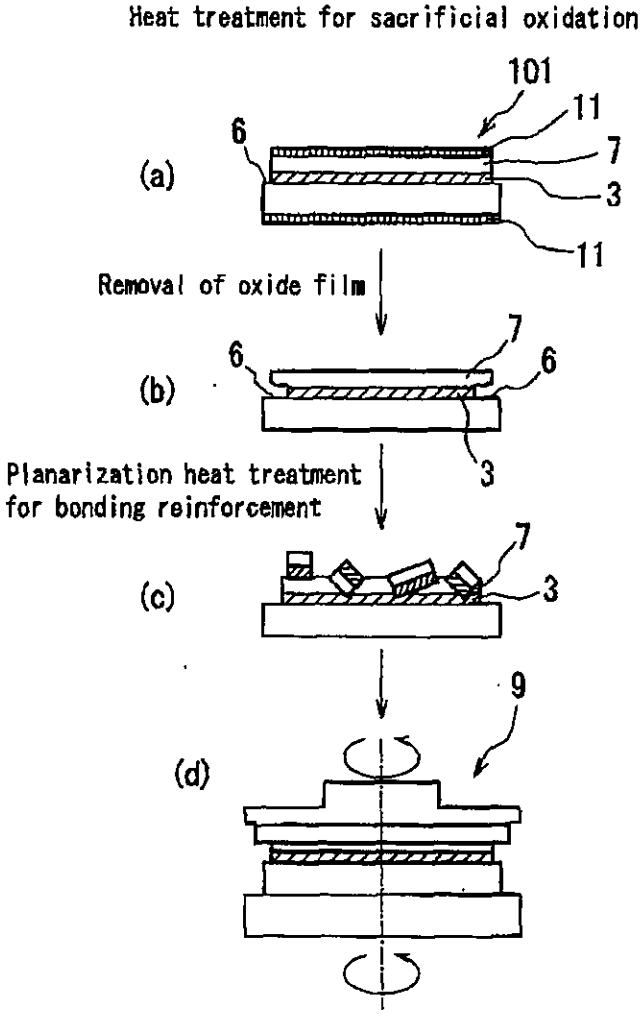

(a)
(b)
Wafer for active layer
1
4
3
H+ implantation
(c)
2
(d)
Wafer for support substrate
1'
4
2'
(e)
5
7
10
(f)
First heat treatment
101
11
7
(g)
3
11
Second heat treatment
(h)
Removal of oxide film
(i)
Planarization
heat treatment
(j)
9
(k)

FIG. 2


Heat treatment for sacrificial oxidation
101
11
6
7
(a)
3
11
Removal of oxide film
7
6
6
(b)
3
Planarization heat treatment
for bonding reinforcement
7
(c)
3
9
(d)